

# Switching (−30V, −9.0A)

## RSS090P03

**●Features**

- 1) Low On-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small and Surface Mount Package (SOP8).

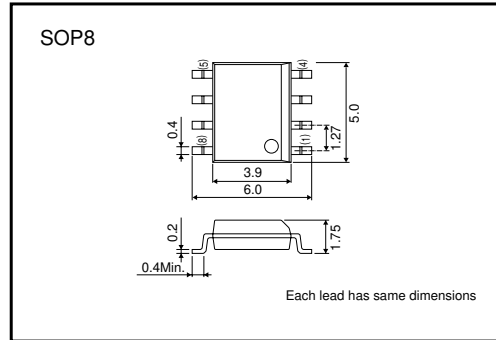
**●Application**

Power switching, DC / DC converter.

**●Structure**

Silicon P-channel  
MOS FET

**●External dimensions (Unit : mm)**



**●Packaging specifications**

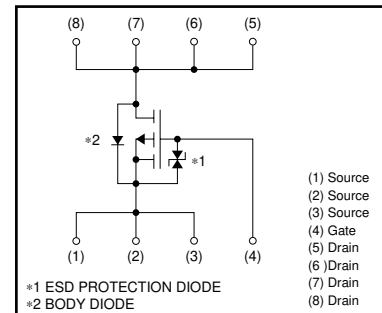
Type	Package	Taping
	Code	TB
	Basic ordering unit (pieces)	2500
RSS090P03		○

**●Absolute maximum ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit
Drain-source voltage	$V_{DSS}$	−30	V
Gate-source voltage	$V_{GSS}$	±20	V
Drain current	Continuous	$I_D$	±9.0 A
	Pulsed	$I_{DP}$	±36 A *1
Source current (Body diode)	Continuous	$I_S$	−1.6 A
	Pulsed	$I_{SP}$	−36 A *1
Total power dissipation	$P_D$	2.0	W *2
Channel temperature	$T_{ch}$	150	°C
Range of Storage temperature	$T_{stg}$	−55 to +150	°C

\*1  $P_{W} \leq 10 \mu s$ , Duty cycle  $\leq 1\%$   
\*2 Mounted on a ceramic board

**●Equivalent circuit**



**●Thermal resistance (Ta=25°C)**

Parameter	Symbol	Limits	Unit
Channel to ambient	$R_{th} (ch-a)$	62.5	°C / W *

\* Mounted on a ceramic board.

## Transistors

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	–	–	$\pm 10$	$\mu A$	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR) DSS}$	–30	–	–	V	$I_D = -1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	–	–	–1	$\mu A$	$V_{DS} = -30V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	–1.0	–	–2.5	V	$V_{DS} = -10V, I_D = -1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	10	14	m $\Omega$	$I_D = -9.0A, V_{GS} = -10V$
		–	15	21	m $\Omega$	$I_D = -4.5A, V_{GS} = -4.5V$
		–	17	23	m $\Omega$	$I_D = -4.5A, V_{GS} = -4.0V$
Forward transfer admittance	$ Y_{fs} $ *	6.0	–	–	S	$V_{DS} = -10V, I_D = -4.5A$
Input capacitance	$C_{iss}$	–	4000	–	pF	$V_{DS} = -10V$
Output capacitance	$C_{oss}$	–	750	–	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{rss}$	–	580	–	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	25	–	ns	$I_D = -4.5A$
Rise time	$t_r$ *	–	50	–	ns	$V_{DD} = -15V$
Turn-off delay time	$t_{d(off)}$ *	–	150	–	ns	$V_{GS} = -10V$
Fall time	$t_f$ *	–	80	–	ns	$R_L=3.3\Omega$
Total gate charge	$Q_g$	–	39	–	nC	$V_{DD} = -15V$
Gate-source charge	$Q_{gs}$	–	7.0	–	nC	$V_{GS} = -5V$
Gate-drain charge	$Q_{gd}$	–	15	–	nC	$I_D = -9.0A$

\*Pulsed

## Body diode characteristics (source-drain characteristics)

Forward voltage	$V_{SD}$	–	–	–1.2	V	$I_S = -1.6A, V_{GS}=0V$
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Transistors

●Electrical characteristic curves

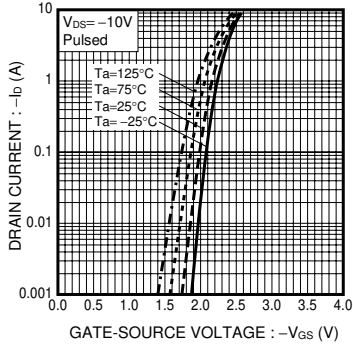


Fig.1 Typical Transfer Characteristics

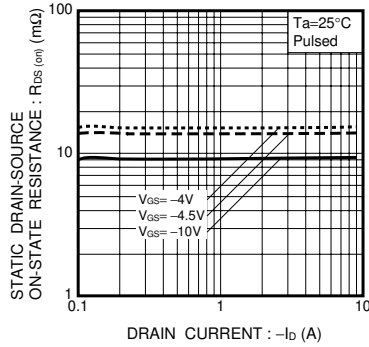


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

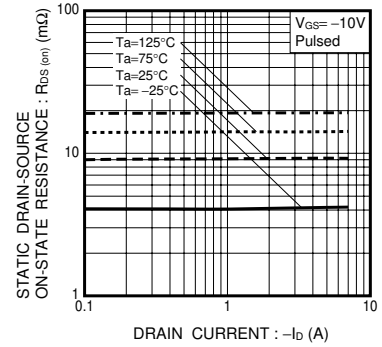


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

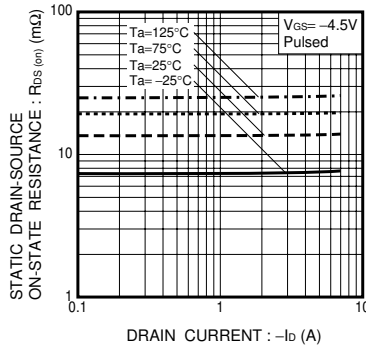


Fig.4 Static Drain-Source On-State vs. Drain Current

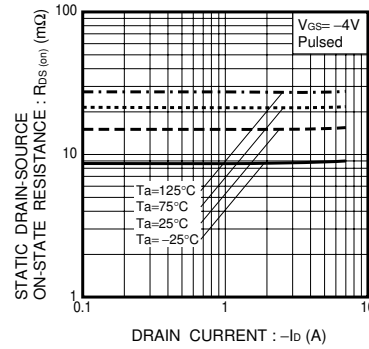


Fig.5 Static Drain-Source On-State vs. Drain Current

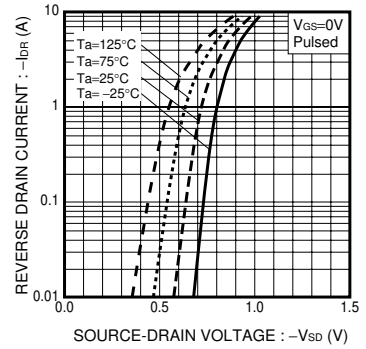


Fig.6 Reverse Drain Current Source-Drain Current

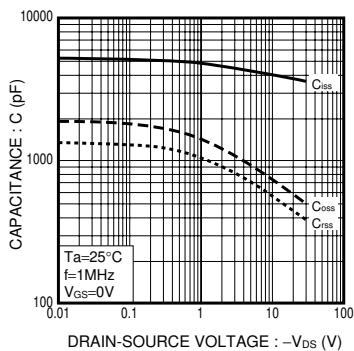


Fig.7 Typical Capacitance vs. Drain-Source Voltage

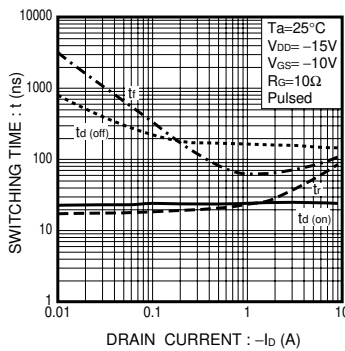


Fig.8 Switching Characteristics

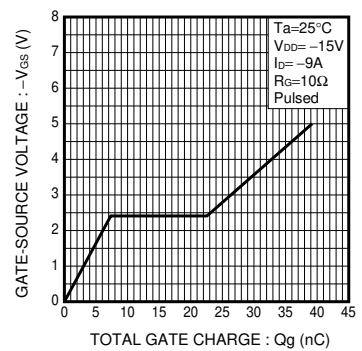


Fig.9 Dynamic Input Characteristics

Transistors

●Measurement circuits

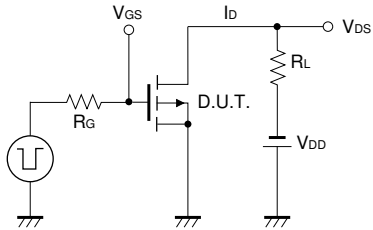


Fig.10 Switching Time Test Circuit

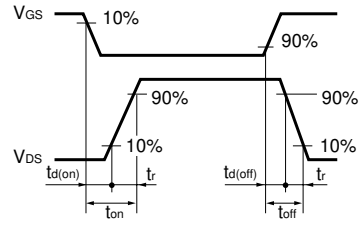


Fig.11 Switching Time Waveforms

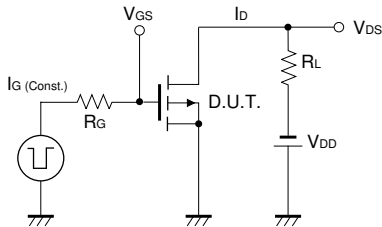


Fig.12 Gate Charge Test Circuit

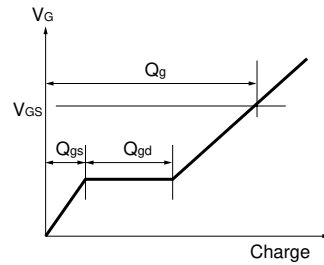


Fig.13 Gate Charge Waveform

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